



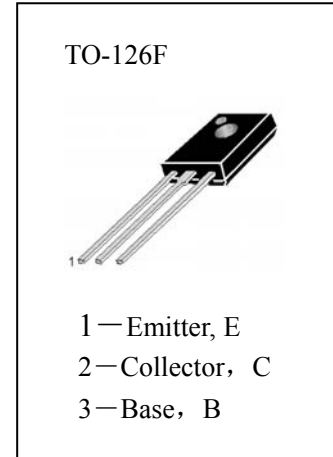
HBD681

APPLICATIONS

Medium Power Linear switching.

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	—Storage Temperature	-65~150°C
T _j	—Junction Temperature	150°C
P _C	—Collector Dissipation (T _c =25°C)	40W
V _{CBO}	—Collector-Base Voltage	100V
V _{CEO}	—Collector-Emitter Voltage	100V
V _{EBO}	—Emitter-Base Voltage	5V
I _C	—Collector Current (Pulse)	6A
I _C	—Collector Current (DC)	4A
I _B	—Base Current	100mA



电参数 (ELECTRICAL CHARACTERISTICS (T_a=25°C))

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I _{CBO}	Collector Cut-off Current			200	μ A	V _{CB} =100V, I _E =0
I _{EBO}	Emitter Cut-off Current			2	mA	V _{EB} =5V, I _C =0
I _{CES}	Collector Cut-off Current			500	μ A	V _{CE} =100V, V _{EB} =0
*H _{FE}	DC Current Gain	750				V _{CE} =3V, I _C =1.5mA
*V _{CE(sat)}	Collector- Emitter Saturation Voltage			2.5	V	I _C =1.5A, I _B =30mA
V _{BE(on)}	Base-Emitter On Voltage			2.5	V	V _{CE} =3V, I _C =1.5A
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	100				I _C =50mA, I _B =0

* Pulse Test:PW=300μS,Duty Cycie=1.5% Pulsed

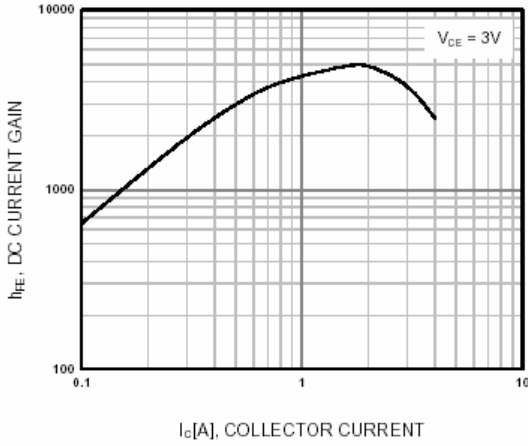
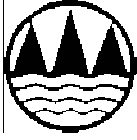


Figure 1. DC current Gain

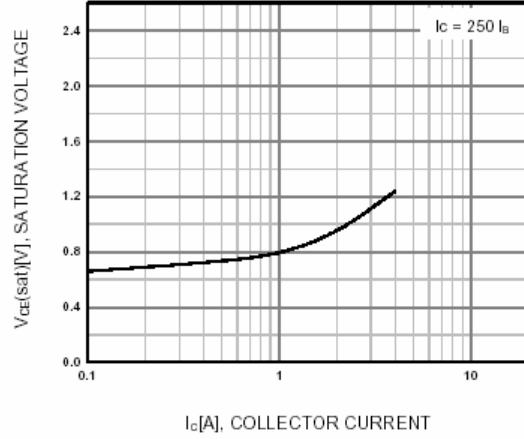


Figure 2. Collector-Emitter Saturation Voltage

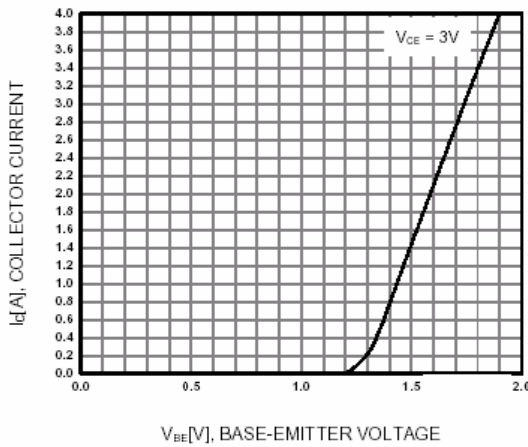


Figure 3. Base-Emitter On Voltage

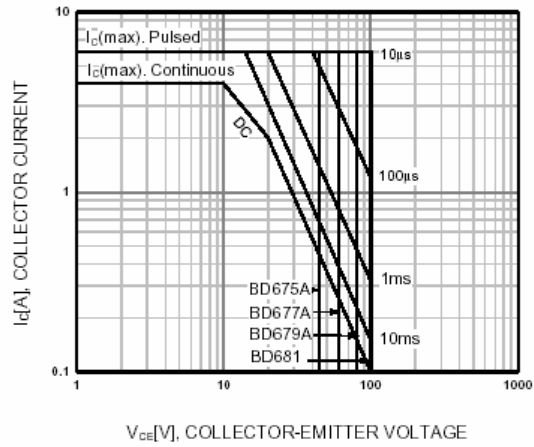


Figure 4. Safe Operating Area

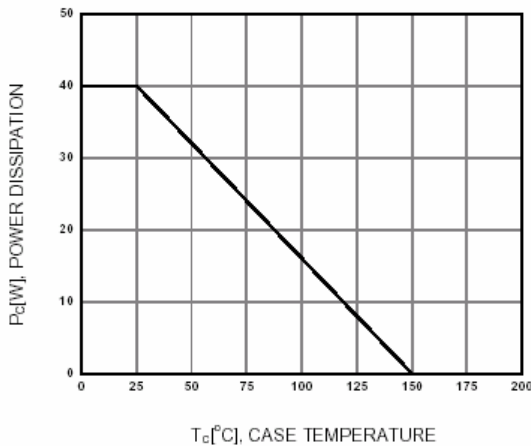


Figure 5. Power Derating